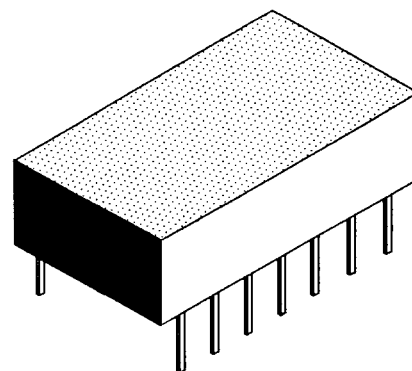


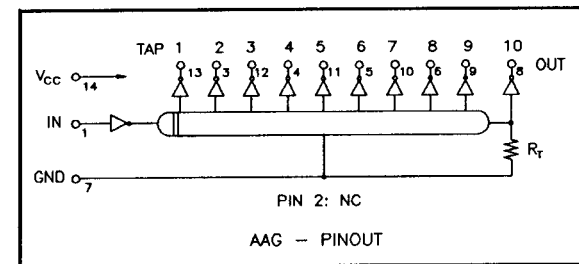
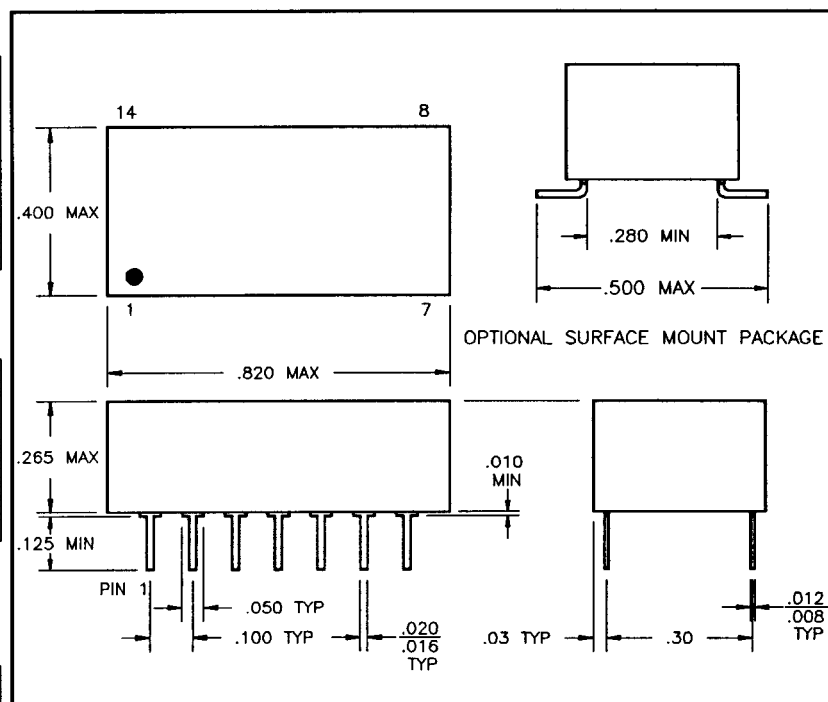
DC Electrical Characteristics		Test Conditions	Min	Max	Unit
Parameter					
V _{OH}	High-Level Output Voltage	V _{CC} =min. V _L =max. I _{OH} =max	2.7		V
V _{OL}	Low Level Output Voltage	V _{CC} =min. V _{IH} =min. I _{OL} =max		0.5	V
V _{IK}	Input Clamp Voltage	V _{CC} =min. I _I =-18mA		-1.2	V
I _{IH}	High-Level Input Current	V _{CC} =max. V _{IN} =2.7V		50	uA
I _{IL}	Low-Level Input Current	V _{CC} =max. V _{IN} =5.25V		1.0	mA
I _{OS}	Short Circuit Output Current	V _{CC} =max. V _{IN} =0.5V	-40	-100	mA
		(One output at a time)			
I _{CC}	High-Level Supply Current	V _{CC} =max. V _{IN} =OPEN		150	mA
I _{CL}	Low-Level Supply Current	V _{CC} =max. V _{IN} =0		150	mA
T _{RO}	Output Rise Time	T _d ≤ 500nS (0.75 to 2.4 Volts)		4	nS
		T _d > 500nS		5	nS
N _H	Fanout High-Level Output	V _{CC} =max. V _{OH} =2.7V		20 TTL LOAD	
N _L	Fanout Low-Level Output	V _{CC} =max. V _{OH} =0.5V		10 TTL LOAD	



Recommended Operating Conditions		Min	Max	Unit
V _{CC}	Supply Voltage	4.75	5.25	V
V _{IH}	High-level Input voltage	2.0		V
V _{IL}	Low-Level Input Voltage		0.8	V
I _{OH}	High-Level Output Current		-1.0	mA
I _{OL}	Low-Level Output Current		20	mA
PW	Pulse Width % of Total Delay	40		%
T _A	Operating Free-Air Temperature	-55	+125	°C

Input Pulse Test Conditions @ 25°C		Unit
E _{IN}	Pulse Input Voltage	3.2 Volts
PW	Pulse Width % of Total Delay	110 %
TRI	Pulse Rise Time (0.75 - 2.4 Volts)	2.0 nS
PRR	Pulse Repetition Rate @ T _d ≤ 200 nS	1.0 MHz
	Pulse Repetition Rate @ T _d > 200 nS	100 KHz
V _{CC}	Supply Voltage	5.0 Volts

ADD "S" SUFFIX TO P/N, TO ORDER SURFACE MOUNT PACKAGE.



TOTAL DELAYS 2 nS ± 5%	TAP DELAYS ± 2 nS OR 5%	POLARA P/N AAG - PINOUT
50	5	AAG-0050
100	10	AAG-0100
150	15	AAG-0150
200	20	AAG-0200
250	25	AAG-0250
300	30	AAG-0300
500	50	AAG-0500

This unit uses a custom designed, hermetically sealed ceramic semiconductor package that meets MIL-M-38510, Paragraph 3.5.1.